





75V DUAL NPN HIGH GAIN MEDIUM POWER TRANSISTOR IN SM-8

Features

- BV_{CEO} > 75V
- I_C = 5A High Collector Current
- I_{CM} = 20A Peak Pulse Current
- High Gain h_{FE} > 300 @ 1A
- Low Saturation Voltage V_{CE(SAT)} < 150mV @ 1A
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- · Qualified to AEC-Q101 Standards for High Reliability

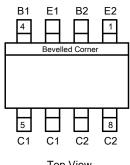
Mechanical Data

- Case: SM-8 (8 LEAD SOT223)
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.117 grams (Approximate)

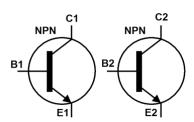


SM-8

Top View



Top View Pin Out



Equivalent Circuit

Ordering Information (Note 4)

ı	Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ı	ZDT1053TA	AEC-Q101	T1053	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

 ZETEX ≥

 T1053 >

SM-8

T1053 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01 to 53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	NPN	Unit
Collector-Base Voltage	V _{CBO}	150	V
Collector-Emitter Voltage	V _{CEO}	75	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	5	Α
Peak Pulse Current	I _{CM}	20	Α
Base Current	I _B	500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Collector Power Dissipation	(Note 5)	D	2.25	W	
Collector Fower Dissipation	(Note 6)	P _D	2.75		
Thermal Resistance, Junction to Ambient	(Note 5)	0	55.6	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	45.5	C/VV	
Thermal Resistance, Junction to Leads (Note 7)		$R_{ heta JL}$	30.7	°C/W	
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to +150	°C		

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

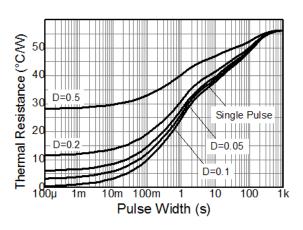
Notes:

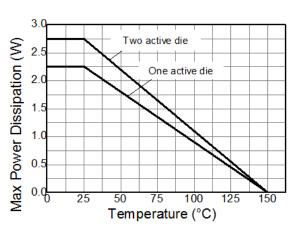
- 5. For a device with any single die active and mounted with the collector lead on 25mm x 25mm 2oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in steady-state.
- Same as Note 5, except both die are active and equally sharing power.
 Thermal resistance from junction to solder-point (at the end of the collector lead).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.





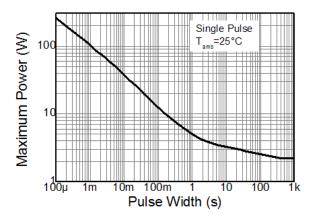
Thermal Characteristics and Derating Information





Transient Thermal Impedance

Derating Curve



Pulse Power Dissipation





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

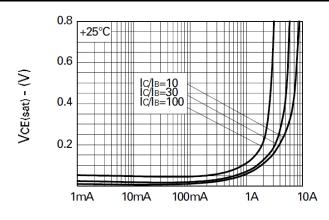
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	150	245	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	75	100	_	V	$I_C = 10mA$
Collector-Emitter Breakdown Voltage	BV _{CES}	150	245	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage	BV _{CEV}	150	245	_	V	$I_C = 100 \mu A, V_{EB} = 1 V$
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.8	_	V	I _E = 100μA
Collector Cut-Off Current	I _{CBO}	_	<1	10	nA	V _{CB} = 120V
Emitter Cut-Off Current	I _{EBO}	_	<1	10	nA	V _{EB} = 5.6V
Collector Emitter Cut-Off Current	I _{CES}	_	<1	10	nA	V _{CES} = 120V
		260	420	_		I _C = 10mA, V _{CE} = 2V
		300	450	1200		IC = 1A, VCE = 2V IC = 2A, VCE = 2V IC = 5A, VCE = 2V IC = 10A, VCE = 2V
DC Current Transfer Static Ratio (Note 9)	h _{FE}	150	220	-		
		30	50	_		
		_	15	_		
	V _{CE(sat)}	_	17	25		$I_C = 0.2A, I_B = 20mA$ $I_C = 1A, I_B = 50mA$
		_	70	100		
Collector-Emitter Saturation Voltage (Note 9)		_	120	150	mV	$I_C = 1A, I_B = 10mA$
		_	150	200		$I_C = 2A$, $I_B = 50mA$
		_	300	440		$I_C = 5A$, $I_B = 250mA$
Base-Emitter Saturation Voltage (Note 9)	V _{BE(SAT)}	_	1100	1200	mV	$I_C = 5A$, $I_B = 250mA$
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(ON)}	_	1000	1100	mV	$I_C = 5A, V_{CE} = 2V$
Transitional Frequency	f⊤	_	140	_	MHz	I _C = 50mA, V _{CE} = 10V, f = 100MHz
Output Capacitance	C _{OBO}	_	21	30	pF	V _{EB} = 10V, f = 1MHz
Suitabing Time	t _{ON}		90	ns $V_{CC} = 50V$,		V _{CC} = 50V, I _C = 2A,
Switching Time	t _{OFF}	_	750	_	ns	$I_{B1} = -I_{B2} = 20mA$

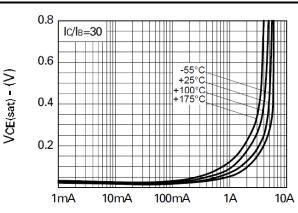
Note:

9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

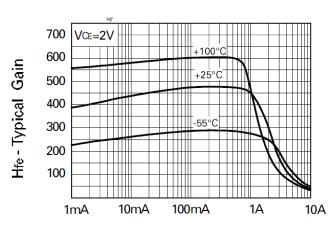


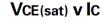


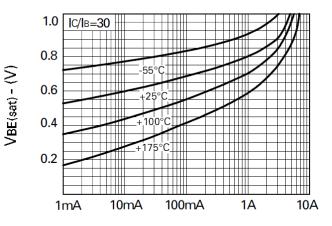
IC-Collector Current

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VCE(sat) v IC



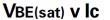


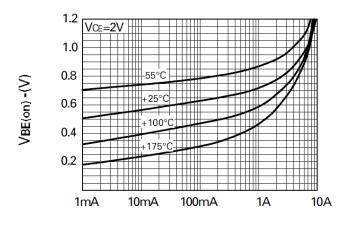


IC-Collector Current

IC-Collector Current

hfe v lc





IC-Collector Current

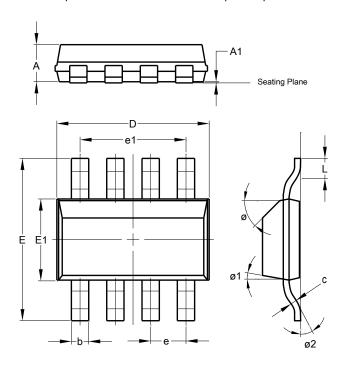
VBE(on) v IC





Package Outline Dimensions

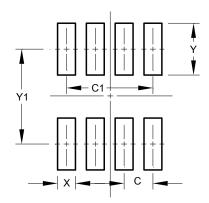
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SM-8						
Dim	Min	Max	Тур			
Α		1.70	1.60			
A1	0.02	0.10	0.04			
b	0.70	0.90	0.80			
C	0.24	0.32	0.28			
D	6.30	6.70	6.60			
е	1.53 REF					
e1	4.59 REF					
Е	6.70	7.30	7.00			
E1	3.30	3.70	3.50			
L	0.75	1.00	0.90			
Ø			45°			
Ø1	1	15°				
Ø2			10°			
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	1.52
C1	4.60
Х	0.95
Υ	2.80
Y1	6.80





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